Analog Power AM5931P

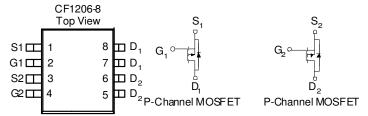
P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r _{DS(on)} provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe CF1206-8 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
$oxed{V_{DS}(V) \qquad r_{DS(on)}(OHM) \qquad I_D(A)}$					
-30	$0.084 @ V_{GS} = -10V$	-3.1			
-30	$0.130 @ V_{GS} = -4.5V$	-2.5			



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Paramete r	Symbol	Maximum	Units			
Drain-Source Voltage			-30	V		
Gate-Source Voltage			±20	V		
Continue Davis Consulta	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	${ m I}_{ m D}$	-3.1			
Continuous Drain Current ^a TA		1D	-2.5	A		
Pulsed Drain Current ^b	I_{DM}	-10				
Continuous Source Current (Diode Conduction) ^a		I_S	±1.6	A		
Power Dissipation ^a	$T_A=25^{\circ}C$	P_{D}	1.15	$_{ m W}$		
Power Dissipation	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1 D	0.7	**		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS								
Parameter	Symbol	Тур	Max					
Mariana Tanadian da Analiand ^a	t <= 10 sec	R_{thJA}	93	110	°C/W			
Maximum Junction-to-Ambient ^a	Steady State		130	150				

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

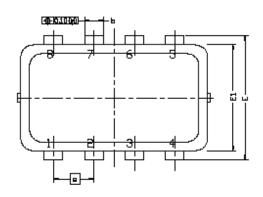
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Donometer	Crymah al	T-4 C 114	Limits			T 1 24	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1.00				
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +/-20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS} -	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Diani Current	¹ DSS	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-3			A	
Drain-Source On-Resistance ^A		$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$			0.084	Ω	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -1.2 \text{ A}$			0.130		
Forward Tranconductance ^A	${f g}_{ m fs}$	$V_{DS} = -5 \text{ V}, I_{D} = -2.5 \text{ A}$		3		S	
Diode Forward Voltage	V_{SD}	$I_S = -1.6 \text{ A}, V_{GS} = 0 \text{ V}$		-0.70		V	
Dynamic ^b	-		-		-	-	
Total Gate Charge	Q_{g}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V},$		6.0			
Gate-Source Charge	Q_{gs}	$I_{DS} = -3 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -2.5 \text{ A}$		0.80		nC	
Gate-Drain Charge	Q_{gd}	$I_{\rm D} = -2.3~{\rm A}$		1.30			
Turn-On Delay Time	$t_{d(on)}$			6.5			
Rise Time	$t_{\rm r}$	$V_{DD} = -5 \text{ V}, R_L = 5 \text{ OHM},$		20		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_G = 6 \text{ OHM}$		31		ns	
Fall-Time	$t_{ m f}$			21			

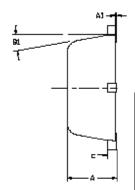
Notes

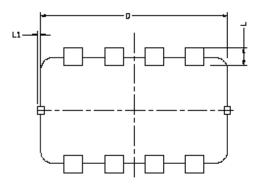
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information







אנע.	MOL	LIMETE	RS		INCHES	;	
	MEN	NOM	MAX	MIN	NOM	MAX	
A	Q700	0.80	מפגם	0.0276	0.0315	0.0334	
Al			005	0.000		0.002	
b	0.24	0.30	<u> 3</u> 3	0.019	0.012	0.014	
C	91.0	0.152	25	0003	0,006	0.010	
D	3.00 BSC			0.11B BSC			
E	2.00 BSC 0.079 BSC)C	
E1	1.70 BSC 0.067 BSC)C	
P	0.65 BSC			0,026 HSC			
L	0.20	0.275	0.400	0,000	0.011	0.0157	
L1	Ů		0.100	đ		0.004	
61	Ü,	П,	12*	Ů'	10,	12"	